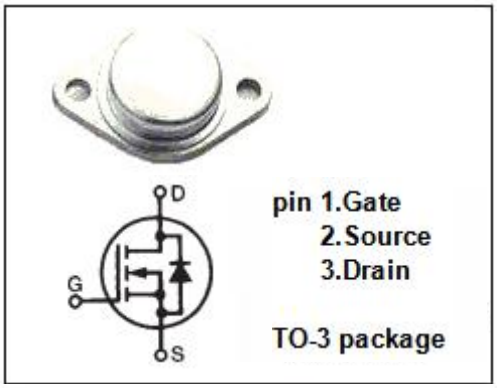
isc N-Channel MOSFET Transistor IXTM11N80

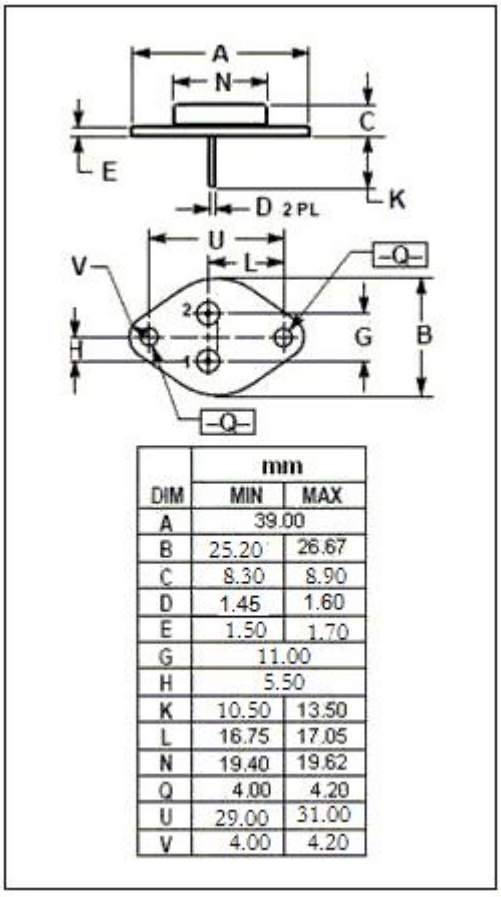
FEATURES

- Drain Current I_D= 11A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 800V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 0.95Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



DESCRIPTION

- Designed for use in switch mode power supplies and general purpose applications.



DIM	mm MIN	MAX
A	39.00	
B	25.20	26.67
C	8.30	8.90
D	1.45	1.60
E	1.50	1.70
G	11.00	
H	5.50	
K	10.50	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	29.00	31.00
V	4.00	4.20

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	11	A
I_{DM}	Drain Current-Single Pluse	44	A
P_D	Total Dissipation @T_C=25℃	300	W
T_J	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	0.42	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 250μA	800		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 250μA	2	4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 5.5A		0.95	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 640V; V_{GS}= 0 V_{DS}= 640V; V_{GS}= 0;T_J=125℃		250 1000	μA
V_{SD}	Forward On-Voltage	I_S= 11A; V_{GS}= 0		1.5	V